TOSHIBA

TOSHIBA DIODE SILICON EPITAXIAL PLANAR TYPE

1 S S 2 5 0

HIGH SPEED SWITCHING APPLICATIONS.

• Low Forward Voltage : V_F(2)=0.90V (Typ.)

• Fast Reverse Recovery Time: trr=60ns (Max.)

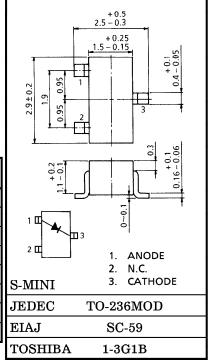
• Small Total Capacitance : C_T=1.5pF (Typ.)

• Small Package : SC-59

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Peak Reverse Voltage	V_{RM}	250	V
Reverse Voltage	$V_{\mathbf{R}}$	200	V
Peak Forward Current	I_{FM}	300	mA
Average Forward Current	IO	100	mA
Surge Current (10ms)	I_{FSM}	2	Α
Power Dissipation	P	150	mW
Junction Temperature	Tj	125	°C
Storage Temperature Range	$T_{ m stg}$	-55~125	°C

Unit in mm



Weight: 0.012g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

			9	0		
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	V _{F (1)}	$I_{ m F} = 10 { m mA}$	_	0.72	1.00	V
	$V_{F(2)}$	$I_{\rm F} = 100 {\rm mA}$	_	0.90	1.20	
Reverse Current	$I_{R(1)}$	$V_R = 50V$		_	0.1	μ A
	$I_{R(2)}$	V_R =200 V		_	1.0	
Total Capacitance	C_{T}	$V_R=0$, f=1MHz	_	1.5	3.0	рF
Reverse Recovery Time	$t_{ m rr}$	I _F =10mA (Fig.1)	_	10	60	ns

Fig1. REVERSE RECOVERY TIME (trr) TEST CIRCUIT

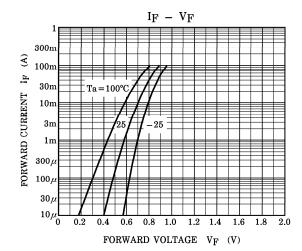
 $(R_{OUT} = 50\Omega)$

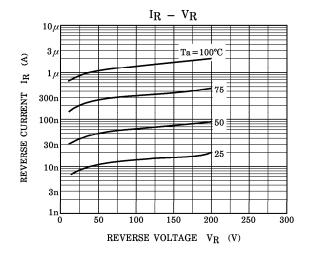
INPUT WAVEFORM $0.01\mu F \text{ DUT}$ $0.01\mu F \text{ DUT}$ 1F = 10mA $0.1 I_R$ $0.1 I_R$

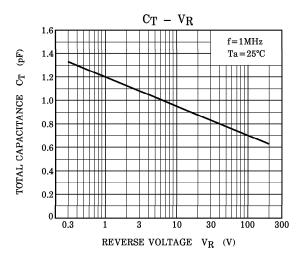
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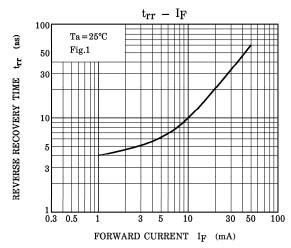
MARKING

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